Complementary Power Transistors

D²PAK for Surface Mount

Complementary power transistors are for general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifiers.

Features

- Low Collector–Emitter Saturation Voltage V_{CE(sat)} = 1.0 V (Max) @ 8.0 A
- Fast Switching Speeds
- Complementary Pairs Simplifies Designs
- Epoxy Meets UL 94 V-0 @ 0.125 in
- ESD Ratings: Human Body Model, 3B > 8000 V Machine Model, C > 400 V
- NJV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- Pb–Free Packages are Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Emitter-Base Voltage	V _{EB}	5	Vdc
Collector Current – Continuous – Peak	Ι _C	10 20	Adc
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	50 0.4	W W/°C
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	2.0 0.016	W ₩/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to 150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	2.5	°C/W	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	75	°C/W	

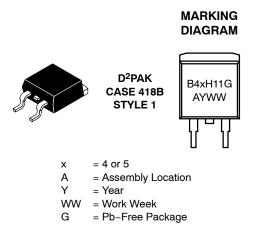
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

http://onsemi.com

SILICON POWER TRANSISTORS 10 AMPERES, 80 VOLTS, 50 WATTS



ORDERING INFORMATION

Device	Package	Shipping [†]
MJB44H11G	D ² PAK (Pb-Free)	50 Units/Rail
MJB44H11T4G	D ² PAK (Pb–Free)	800/Tape & Reel
NJVMJB44H11T4G	D ² PAK (Pb–Free)	800/Tape & Reel
MJB45H11G	D ² PAK (Pb-Free)	50 Units/Rail
MJB45H11T4G	D ² PAK (Pb-Free)	800/Tape & Reel
NJVMJB45H11T4G	D ² PAK (Pb–Free)	800/Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T _C = 25°C unless otherwise noted)						
Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector-Emitter Sustaining Voltage ($I_C = 30$ mA, $I_B = 0$)		V _{CEO(sus)}	80	-	-	Vdc
Collector Cutoff Current (V_{CE} = Rated V_{CEO} , V_{BE} = 0)		ICES	-	-	10	μΑ
Emitter Cutoff Current (V _{EB} = 5 Vdc)		I _{EBO}	-	-	50	μΑ
ON CHARACTERISTICS						•
Collector-Emitter Saturation Voltage (I _C = 8 Adc, I _B = 0.4 Adc)		V _{CE(sat)}	-	-	1.0	Vdc
Base–Emitter Saturation Voltage ($I_C = 8$ Adc, $I_B = 0.8$ Adc)		V _{BE(sat)}	-	-	1.5	Vdc
DC Current Gain (V _{CE} = 1 Vdc, I _C = 2 Adc)		h _{FE}	60	-	-	-
DC Current Gain (V _{CE} = 1 Vdc, I _C = 4 Adc)			40	-	-	
DYNAMIC CHARACTERISTICS						
Collector Capacitance (V _{CB} = 10 Vdc, f_{test} = 1 MHz) MJB44H11, NJVMJB44H11 MJB45H11, NJVMJB45H11	C _{cb}		130 230		pF
Gain Bandwidth Product (I_C = 0.5 Adc, V_{CE} = 10 Vo	dc, f = 20 MHz) MJB44H11, NJVMJB44H11 MJB45H11, NJVMJB45H11	f _T		50 40		MHz
SWITCHING TIMES						•
Delay and Rise Times($I_C = 5 \text{ Adc}$, $I_{B1} = 0.5 \text{ Adc}$)	MJB44H11, NJVMJB44H11 MJB45H11, NJVMJB45H11	t _d + t _r		300 135		ns
Storage Time(I _C = 5 Adc, I _{B1} = I _{B2} = 0.5 Adc)	MJB44H11, NJVMJB44H11 MJB45H11, NJVMJB45H11	t _s		500 500		ns
Fall Time(I _C = 5 Adc, I _{B1} = I _{B2} = 0.5 Adc)	MJB44H11, NJVMJB44H11 MJB45H11, NJVMJB45H11	t _f		140 100		ns

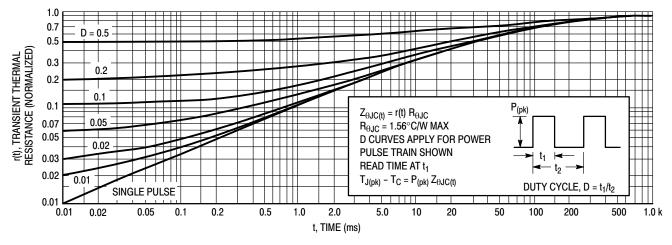


Figure 1. Thermal Response

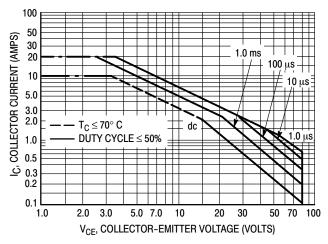
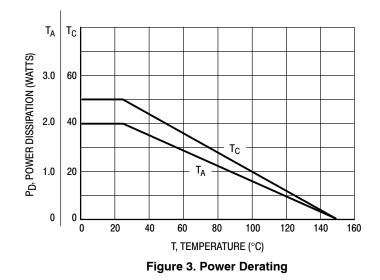
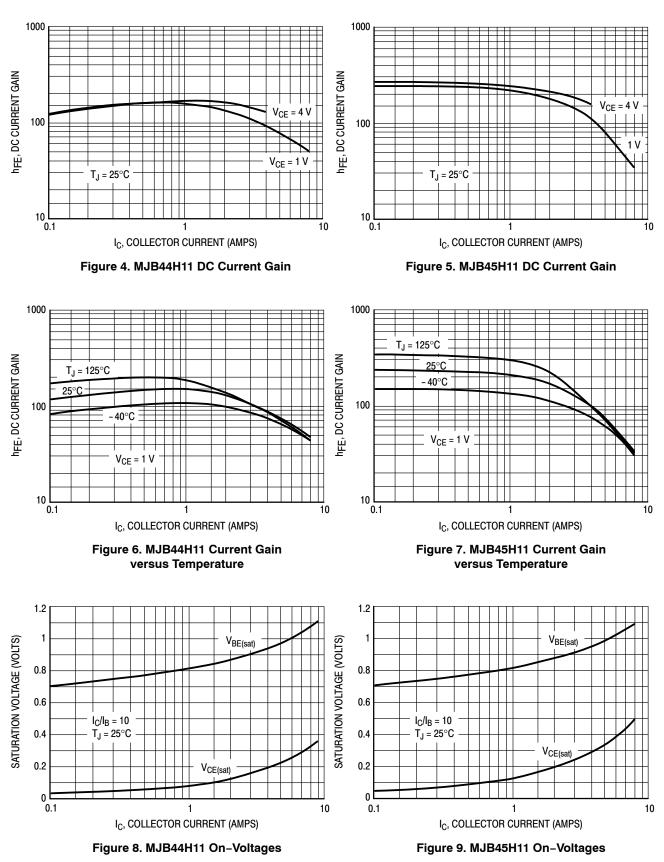


Figure 2. Maximum Rated Forward Bias Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate I_C – V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \le 150^{\circ}C$. $T_{J(pk)}$ may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.





9.65

10.29

4.83

0.89

1.40

8.89

2.79

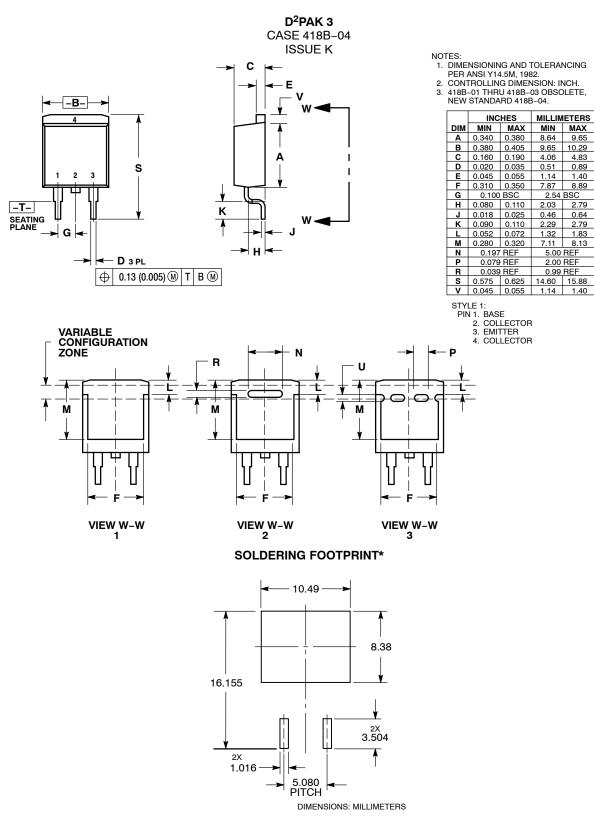
0.64

2.79

1.83

8.13

PACKAGE DIMENSIONS



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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